

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	12	(bit adj line adj contact) and (polysilicon near3 spacer) and (remov\$3 near3 spacer) and (etch near3 dielectric) and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 12:09
S2	95	(bit adj line adj contact) and (polysilicon adj spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 12:09
S3	87	S2 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 13:57
S4	45	(gate adj electrode) near3 (polysilicon adj spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 13:59
S5	44	S4 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 13:57
S6	56	(gate adj electrode) near3 ((polysilicon (polycrystalline adj silicon) poly) adj spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 14:32
S7	54	S6 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 13:59
S8	93	(gate adj electrode) near3 ((polysilicon (polycrystalline adj silicon) poly) adj2 spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 14:33

S9	89	S8 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 14:35
S10	6	S9 and (bit adj line adj contact)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 15:06
S11	6	S9 and (((bit adj line) bitline) adj contact)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/20 16:12
S16	8855	spacer near2 remov\$2 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/21 16:06
S17	132	(polysilicon adj spacer) near2 remov\$2 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 08:31
S18	662	bit.ti. and line.ti. and contact.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/21 16:13
S19	9	S18 and (polysilicon adj spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/21 16:16
S20	16	S18 and (remov\$2 near2 spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/21 17:23

S21	3	S18 and (portion near2 remov\$2 near2 spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/21 17:38
S22	0	S18 and (remov\$2 near2 (polysilicon adj sidewall))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/21 17:38
S23	1	S18 and (remov\$2 near2 (polysilicon near2 sidewall))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/21 17:44
S26	66	(polysilicon adj spacer) near2 etch and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:01
S28	0	cap near3 (gate adj electrode) and (polysilicon adj spacer) and (etch adj selectivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:51
S29	1	cap near3 (gate adj electrode) and (polysilicon adj spacer) and (etch\$3 adj selectivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:51
S30	83	(polysilicon adj spacer) and (etch\$3 adj selectivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:52
S31	78	S30 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:51

S32	6	(polysilicon adj spacer) near5 (etch\$3 adj selectivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:53
S33	1	(polysilicon adj spacer) and ((etch\$3 adj selectivity) adj3 "50")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:54
S34	0	(etch\$3 adj selectivity) adj3 "50 to 1"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:55
S35	0	(etch\$3 adj selectivity) adj3 fifty	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:55
S36	28	(etch\$3 adj selectivity) adj3 "50:1"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 09:56
S37	17	S36 and polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 10:02
S38	110	(silicon adj nitride) near2 (polysilicon (polycrystalline silicon)) near2 (etch adj selectivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 15:50
S39	214	(silicon adj nitride) near2 (polysilicon (polycrystalline silicon)) near2 (etch\$3 adj selectivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 10:03

S40	177	S39 and @ad<="20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 10:03
S41	19	(silicon adj nitride) near2 (polysilicon (polycrystalline adj silicon)) near2 (etch\$3 adj selectivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 10:03
S42	15	S41 and @ad<="20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 10:53
S43	2	(silicon adj nitride adj liner) near3 RIE	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:13
S46	327	barrier adj spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:02
S48	2	(silicon adj nitride) near2 (polysilicon (polycrystalline silicon)) near2 (etch adj selectivity) and 50:1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 08:53
S49	110	(silicon adj nitride) near2 (polysilicon (polycrystalline silicon)) near2 (etch adj selectivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 08:33
S50	13	(silicon adj nitride) near2 (polysilicon (polycrystalline adj silicon)) near2 (etch adj selectivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 09:39

S51	48	(silicon adj nitride) near2 (polysilicon (polycrystalline adj silicon)) near2 (etch adj selectivity rate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 08:45
S52	22	(silicon adj nitride) near2 (polysilicon (polycrystalline adj silicon)) near2 (etch adj rate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 08:49
S53	696	MERIE	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 08:49
S54	7	MERIE same (polysilicon and silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 08:50
S57	9	(silicon adj nitride) near2 (polysilicon (polycrystalline silicon)) near2 (etch adj rate) and 100:1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 09:35
S58	1	@pn="6787415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 09:36
S59	26	(silicon adj nitride) near3 (polysilicon) near3 (etch adj rate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:56
S60	40	(silicon adj nitride) near5 (polysilicon) near5 (etch adj rate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:02

S61	38	S60 and @ad<="20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:03
S62	0	(silicon adj nitride) near3 (polysilicon) near3 100:1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:13
S63	26	(silicon adj nitride) near3 (polysilicon) near3 "100"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:14
S64	24	S63 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:14
S66	8	(silicon adj nitride) near3 (polysilicon) near3 etch\$3 near3 "100" and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:17
S67	0	(silicon adj nitride) near3 (polysilicon) near3 etch\$3 near3 50:1 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:18
S68	0	(silicon adj nitride) near5 (polysilicon) near5 etch\$3 near3 50:1 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:18
S69	0	(silicon adj nitride) near5 (polysilicon) near5 etch\$3 near3 100:1 and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 10:18

S70	0	(silicon adj nitride) near5 (polysilicon) near5 etch\$3 near3 fifty and @ad<"20030415"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 12:49
S71	10	gate near3 cap\$4 near8 spacer near5 (etch adj (rate selectivity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 12:49
S72	0	KOH near3 polysilicon near5 (silicon adj nitride) near3 (etch\$3 adj (rate selectivity))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/25 15:57